

IN THE CLAIMS:

Please cancel Claims 1 to 10, without prejudice to or disclaimer of the subject matter presented therein. Please add new Claims 11 to 21, as follows:

1 to 10. (Cancelled)

11. (New) A method of manufacturing a display device, comprising:

(i) a step of preparing a member by performing the steps of:

(a) forming a porous layer as a separation layer on a surface of a semiconductor substrate,

(b) forming a semiconductor film on a surface of the separation layer, and then

(c) forming a first region with a switching element and a second region with a peripheral circuit in the semiconductor film;

(ii) a step of forming an image display portion on the first region; and

(iii) a separation step of separating the first and second regions from the member together with the image display portion.

12. (New) The method according to claim 11, wherein the semiconductor film is formed on a surface of the porous layer after forming a protective film on inner walls of pores in the porous layer.

13. (New) The method according to claim 11, wherein the semiconductor substrate is a single-crystal silicon substrate or a compound semiconductor substrate.

14. (New) The method according to claim 11, wherein the separation step is executed by injecting a fluid formed from a liquid or gas to or near a side surface of the separation layer.

15. (New) The method according to claim 11, wherein the separation step is executed under a static pressure.

16. (New) The method according to claim 11, wherein the member is formed again using a remaining member which remains after the first and second regions are separated from the member.

17. (New) A method of manufacturing a display device, comprising:

(i) a step of preparing a member by performing the steps of:

(a) forming a first region with a switching element and a second region with a peripheral circuit in a surface of a semiconductor substrate, and then

(b) forming a separation layer in the semiconductor substrate by implanting ions in the semiconductor substrate through the surface of the semiconductor substrate;

(ii) a step of forming an image display portion on the first region; and

(iii) a separation step of separating the first and second regions from the member together with the image display portion.

18. (New) The method according to claim 17, wherein the semiconductor substrate is a single-crystal silicon substrate or a compound semiconductor substrate.

19. (New) The method according to claim 17, wherein the separation step is executed by injecting a fluid formed from a liquid or gas to or near a side surface of the separation layer.

20. (New) The method according to claim 17, wherein the separation step is executed under a static pressure.

21. (New) The method according to claim 17, wherein the member is formed again using a remaining member which remains after the first and second regions are separated from the member.